

# 2MBI550VN-170-50

**IGBT Modules** 

# **IGBT MODULE (V series)** 1700V / 550A / 2 in one package

#### Features

High speed switching Voltage drive Low Inductance module structure

#### Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



#### Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T<sub>c</sub>=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units		
Collec	Collector-Emitter voltage		Vces			1700	V	
Gate-	Gate-Emitter voltage		V <sub>GES</sub>			±20	V	
<u></u>			Ic	Continuous	Tc=25°C	750		
ırte				Continuous	Tc=100°C	550		
Collector current		I <sub>C pulse</sub>	1ms		1100	Α		
		-Ic			550			
			-I <sub>C pulse</sub>	1ms		1100		
Collec	Collector power dissipation		Pc	1 device		3750	W	
Junction temperature		Tj			175	°C		
Operating junction temperature (under switching conditions)		Tjop			150			
Storage temperature		T <sub>stg</sub>			-40 ~ 125			
loolotion	lation voltage	between terminal and copper base (*1)	V	AC : 1min.		3400	VAC	
isolation vo	voitage	between thermistor and others (*2)	V iso	AC . IIIIII.		3400	VAC	
Screw tor	our torque	Mounting (*3)	-			3.5	N m	
Screw tor	ıque	Terminals (*4)	-			4.5	IN III	

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note \*3: Recommendable Value: 2.5-3.5 Nm (M5)

Note \*4: Recommendable Value: 3.5-4.5 Nm (M6)

Electrical characteristics (at T<sub>i</sub>= 25°C unless otherwise specified)

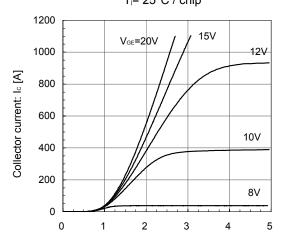
Items		Symbols	Conditions		Characteristics			Units
		Syllibols			min.	typ.	max.	Units
	Zero gate voltage collector current	Ices	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1700V		-	-	3.0	mA
	Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	600	nA
	Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = 20V, I <sub>C</sub> = 550mA		6.0	6.5	7.0	V
		V <sub>CE (sat)</sub> (terminal)	V <sub>GE</sub> = 15V I <sub>C</sub> = 550A	T <sub>j</sub> =25°C	-	2.90	3.35	V
	Collector-Emitter saturation voltage			T <sub>j</sub> =125°C	-	3.45	-	
				T <sub>j</sub> =150°C	-	3.55	-	
		V <sub>CE (sat)</sub> (chip)		T <sub>j</sub> =25°C	-	2.15	2.60	
				T <sub>j</sub> =125°C	-	2.70	-	
				T <sub>j</sub> =150°C	-	2.80	-	
	nternal gate resistance R <sub>G (int)</sub> -			-	1.67	-	Ω	
Ē	Input capacitance	Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz		-	40	-	nF
ē	Turn-on time	ton	Vcc = 900V	-	1000	-	nsec	
Inverter		tr	$I_{C} = 550A$ $V_{GE} = \pm 15V$ $R_{G} = 3.3\Omega$ $L_{S} = 80nH$		-	500		-
		t <sub>r (i)</sub>			-	120		-
	Turn-off time	toff			-	1300		-
	Turn-on time	tf			-	100		-
		V <sub>F</sub> (terminal)		T <sub>j</sub> =25°C	-	2.70	3.15	V
	Forward on voltage		V <sub>GE</sub> = 0V I <sub>F</sub> = 550A	T <sub>j</sub> =125°C	-	3.00	-	
				T <sub>j</sub> =150°C	-	2.95	-	
		V <sub>F</sub> (chip)		T <sub>j</sub> =25°C	-	1.95	2.40	
				T <sub>j</sub> =125°C	-	2.25	-	
				T <sub>j</sub> =150°C	-	2.20	-	
	Reverse recovery time	trr	I <sub>F</sub> = 550A		-	250	-	nsec
jo	Resistance	R	T = 25°C		-	5000	-	Ω
Thermistor			T = 100°C		465	495	520	
≝	B value	В	T = 25/50°C		3305	3375	3450	K

#### Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
items		Conditions	min.	typ.	max.	Units
Thermal register co(4 device)	R <sub>th(j-c)</sub>	Inverter IGBT	-	-	0.04	°C/W
Thermal resistance(1device)		Inverter FWD	-	-	0.06	
Contact thermal resistance (1device) (*5)	R <sub>th(c-f)</sub>	with Thermal Compound	-	0.0167	-	
Contact thermal resistance (1device) (*5)	R <sub>th(c-f)</sub>		-	0.0167		

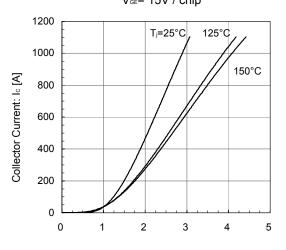
#### ■ Characteristics (Representative)

[INVERTER]
Collector current vs. Collector-Emitter voltage (typ.)
T<sub>i</sub>= 25°C / chip



Collector-Emitter voltage: Vce [V]

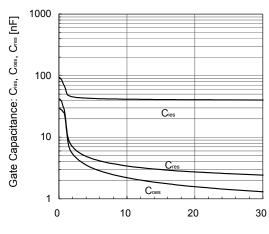
[INVERTER]
Collector current vs. Collector-Emitter voltage (typ.)  $V_{GE}$ = 15V / chip



Collector-Emitter Voltage:  $V_{\text{CE}}[V]$ 

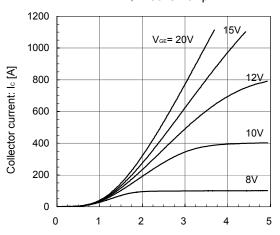
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.)  $V_{GE} = 0V, f = 1MHz, T_{j} = 25^{\circ}C$ 



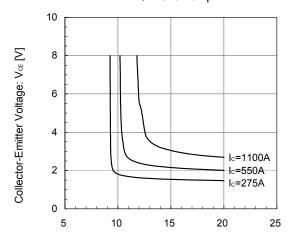
Collector-Emitter voltage: Vce [V]

[INVERTER]
Collector current vs. Collector-Emitter voltage (typ.)
T<sub>i</sub>= 150°C / chip



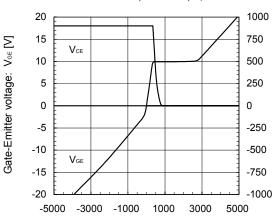
Collector-Emitter voltage: VCE [V]

[INVERTER]
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)  $T_i$ = 25°C / chip



Gate-Emitter Voltage:  $V_{\text{GE}}$  [V]

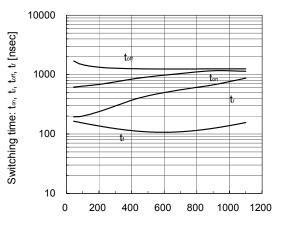
[INVERTER]
Dynamic Gate Charge (typ.)
V₀c=900V, I₀=550A, T₀= 25°C



Gate charge: Q<sub>9</sub> [μC]

#### [INVERTER]

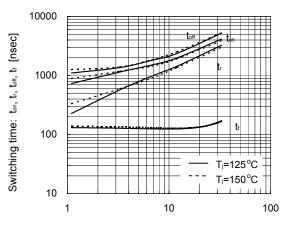
Switching time vs. Collector current (typ.)  $V_{\text{CC}}$ =900V,  $V_{\text{GE}}$ =±15V,  $R_{\text{G}}$ =3.3 $\Omega$ ,  $T_{\text{J}}$ =25°C



Collector current: Ic [A]

#### [INVERTER]

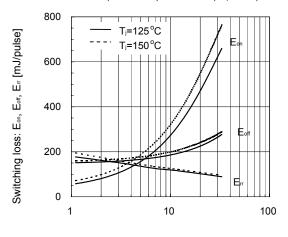
Switching time vs. Gate resistance (typ.)  $V_{cc}$ =900V,  $I_c$ =550A,  $V_{ce}$ =±15V,  $T_j$ =125°C, 150°C



Gate resistance: R<sub>G</sub> [Ω]

#### [INVERTER]

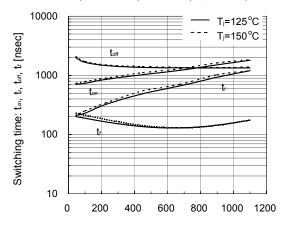
Switching loss vs. Gate resistance (typ.)  $V_{cc}$ =900V,  $I_c$ =550A,  $V_{cE}$ =±15V,  $T_j$ =125, 150°C



Gate resistance: R<sub>G</sub> [Ω]

#### [INVERTER]

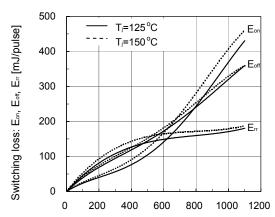
Switching time vs. Collector current (typ.)  $V_{\text{cc}}$ =900V,  $V_{\text{ce}}$ =±15V,  $R_{\text{c}}$ =3.3 $\Omega$ ,  $T_{\text{j}}$ =125°C, 150°C



Collector current: Ic [A]

[INVERTER]

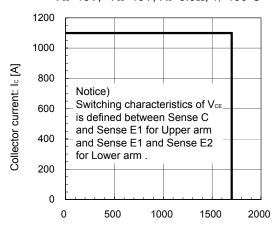
Switching loss vs. Collector current (typ.)  $V_{\text{CC}}$ =900V,  $V_{\text{CE}}$ =±15V,  $R_{\text{G}}$ =3.3 $\Omega$ ,  $T_{\text{J}}$ =125°C, 150°C



Collector current: Ic [A]

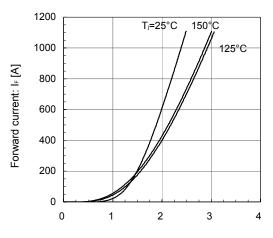
[INVERTER]

Reverse bias safe operating area (max.)  $+V_{GE}=15V$ ,  $-V_{GE}=15V$ ,  $R_{G}=3.3\Omega$ ,  $T_{j}=150^{\circ}C$ 



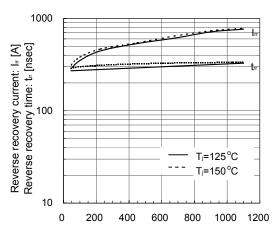
Collector-Emitter voltage: Vce [V]

[INVERTER]
Forward Current vs. Forward Voltage (typ.)
chip



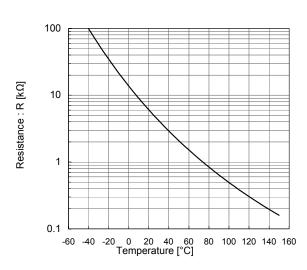
[INVERTER]
Reverse Recovery Characteristics (typ.)
V<sub>cc</sub>=900V, V<sub>cε</sub>=±15V, R<sub>c</sub>=3.3Ω, T<sub>i</sub>=125°C, 150°C

Forward on voltage: V<sub>F</sub> [V]

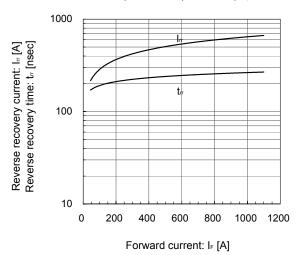


Forward current: I<sub>F</sub> [A]

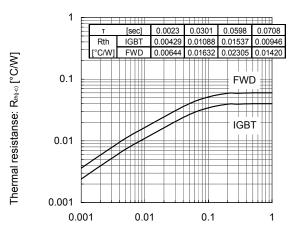
[THERMISTOR]
Temperature characteristic (typ.)



[INVERTER] Reverse Recovery Characteristics (typ.)  $V_{cc}$ =900V,  $V_{ce}$ =±15V,  $R_c$ =3.3 $\Omega$ ,  $T_j$ =25°C

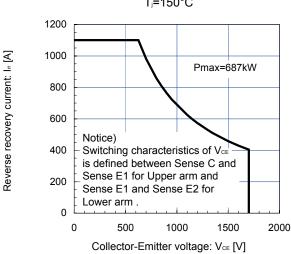


Transient Thermal Resistance (max.)

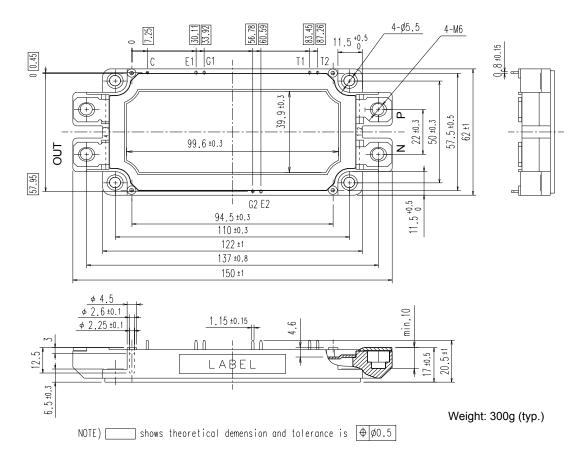


Pulse Width: Pw [sec]

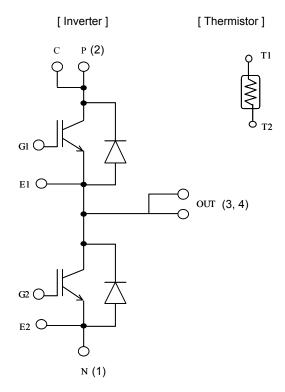
FWD safe operating area (max.)
T=150°C



### ■ Outline Drawings, mm



## **■** Equivalent Circuit Schematic



http://www.fujielectric.com/products/semiconductor/

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